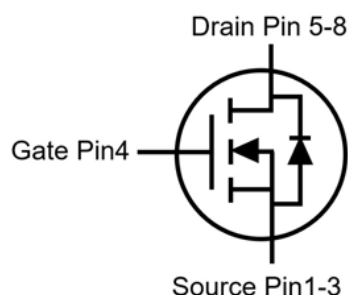
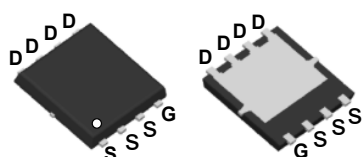


SGT N-channel Power MOSFET

MTR6R7N08SD PDFN5x6



V_{DS}	80	V
$R_{DS(on),TYP@ V_{GS}=10V}$	5.3	mΩ
I_D	80	A

Features

- 1、Low on – resistance
- 2、High power package (PDFN5X6)
- 3、SGT N-channel Power MOSFET

Applications

- 1、Load Switch for Portable Devices
- 2、DC/DC Converter

Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		80	V
V_{GS}	Gate-Source voltage		± 20	V
I_S	Continuous Source Current	$T_C = 25^\circ\text{C}$	--	A
I_D	Continuous drain current @ $V_{GS}=10V$	$T_C = 25^\circ\text{C}$ (Package limit)	80	A
		$T_C = 100^\circ\text{C}$ (Silicon limit)	70	A
I_{DM}	Pulse drain current tested ①	$T_C = 25^\circ\text{C}$	400	A
E_{AS}	Avalanche energy, single pulsed ②		484	mJ
P_D	Maximum power dissipation	$T_C = 25^\circ\text{C}$	220	W
T_{STG}, T_J	Storage and Junction Temperature Range		-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Rating	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	0.76	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	65	°C/W

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
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Static Electrical Characteristics @T_j=25°C (unless otherwise stated)

V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	80	--	--	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V, T _j =25°C	--	--	1	μA
		V _{DS} =80V, V _{GS} =0V, T _j =125°C	--	--	50	μA
IGSS	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2.0	2.9	4.0	V
R _{DS(on)}	Drain-Source On-State Resistance ④	V _{GS} =10V, I _D =20A	--	5.3	6.7	mΩ

Dynamic Electrical Characteristics@T_j = 25°C (unless otherwise stated)

C _{iss}	Input Capacitance	V _{DS} =40V, V _{GS} =0V, f=1MHz	--	3633	--	pF
C _{oss}	Output Capacitance		--	580	--	pF
C _{rss}	Reverse Transfer Capacitance		--	28	--	pF
g _{fs}	Forward Transconductance	V _{DS} = 5V, I _D = 50A	--	80	--	S
R _g	Gate Resistance	f =1MHz	--	1.3	--	Ω
Q _g	Total Gate Charge	V _{DS} =40V, I _D =25A, V _{GS} =10V	--	56.6	--	nC
Q _{gs}	Gate-Source Charge		--	21.4	--	nC
Q _{gd}	Gate-Drain Charge		--	12.5	--	nC

Switching Characteristics

Td(on)	Turn-on Delay Time	T _j =25°C, V _{DS} =40V, V _{GS} =10V, R _L =3Ω	--	17.3	--	ns
Tr	Turn-on Rise Time		--	33	--	ns
Td(off)	Turn-Off Delay Time		--	38.9	--	ns
Tf	Turn-Off Fall Time		--	18.1	--	ns

Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)

VSD	Forward on voltage	I _{SD} =50A, V _{GS} =0V	--	0.85	1.2	V
Trr	Reverse Recovery Time	I _F =20A	--	68	--	ns
Qrr	Reverse Recovery Charge	di/dt=500A/μs	--	66	--	nC

NOTE: ① Repetitive rating; pulse width limited by max junction temperature.
 ② Limited by T_{Jmax}, starting T_J = 25°C, L=0.5mH, R_g=25Ω. Part not recommended for use above this value
 ③ The power dissipation P_{DSM} is based on RθJA and the maximum allowed junction temperature of 150°C.
 ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

Figure 1. Typ. Output Characteristics ($T_J=25^\circ\text{C}$)

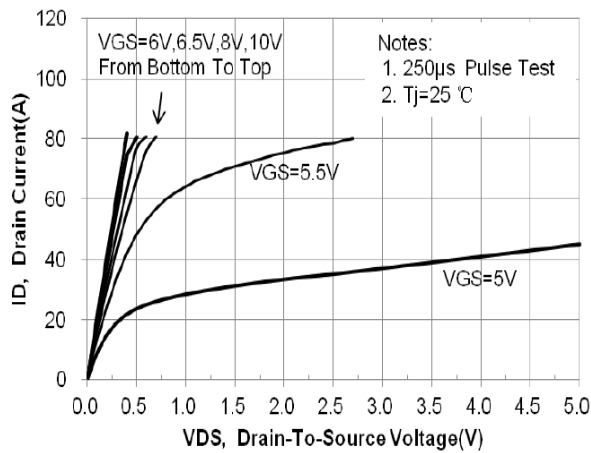


Figure 2. Transfer Characteristics (Junction Temperature)

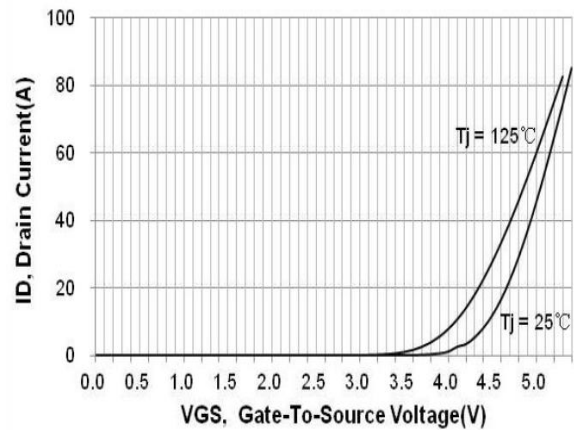


Fig 3: $R_{DS(on)}$ Vs I_{DS} Characteristics ($T_C=25^\circ\text{C}$)

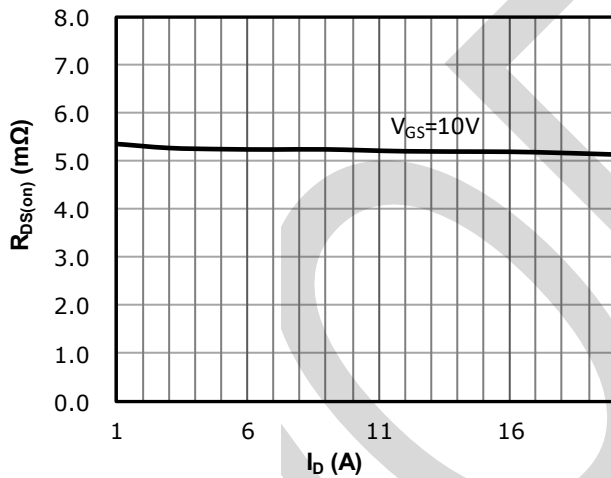


Fig 4: $R_{DS(on)}$ vs Gate Voltage

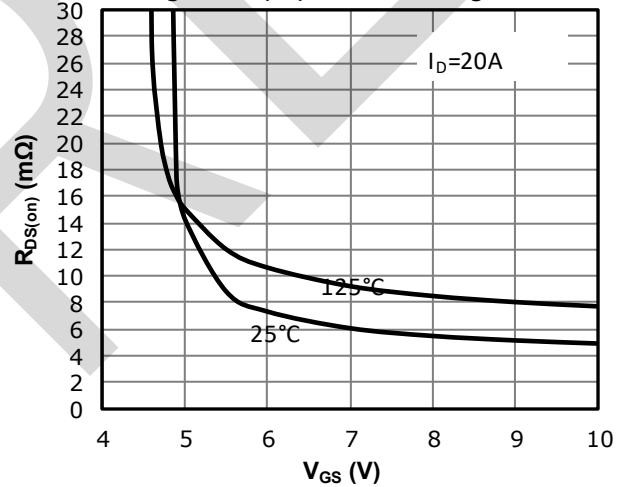


Fig 5: $R_{DS(on)}$ vs. Temperature

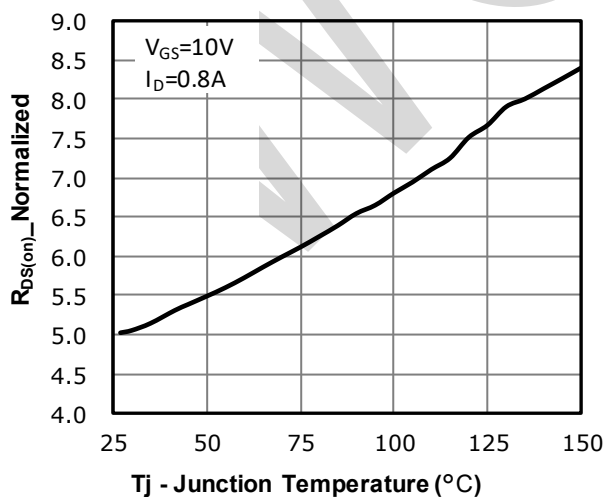
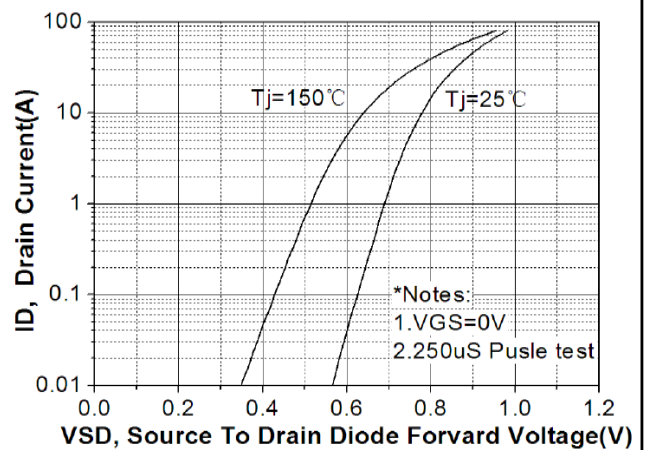


Fig 6: Body-diode Forward Characteristics



Typical Characteristics

Figure 7. Gate-Charge Characteristics

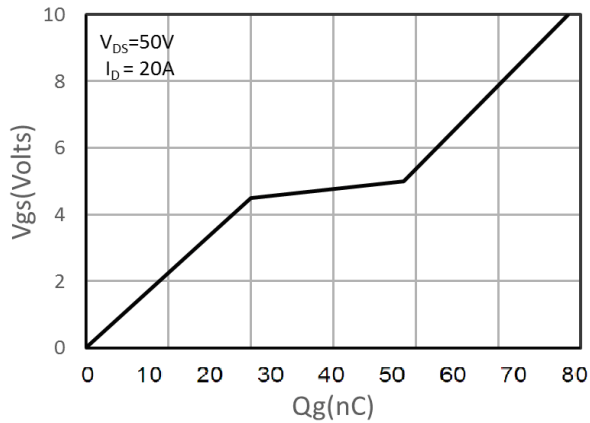


Figure 8. Drain Current Derating

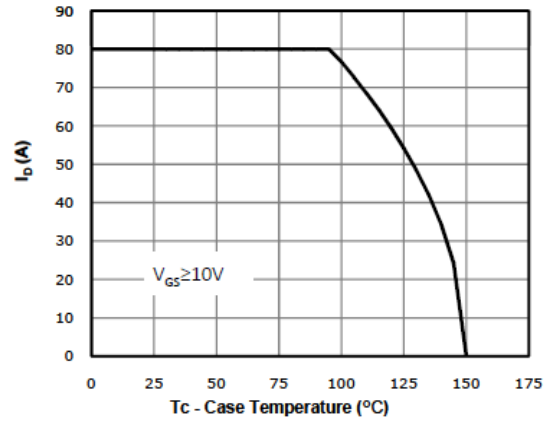


Fig 9: Capacitance Characteristics

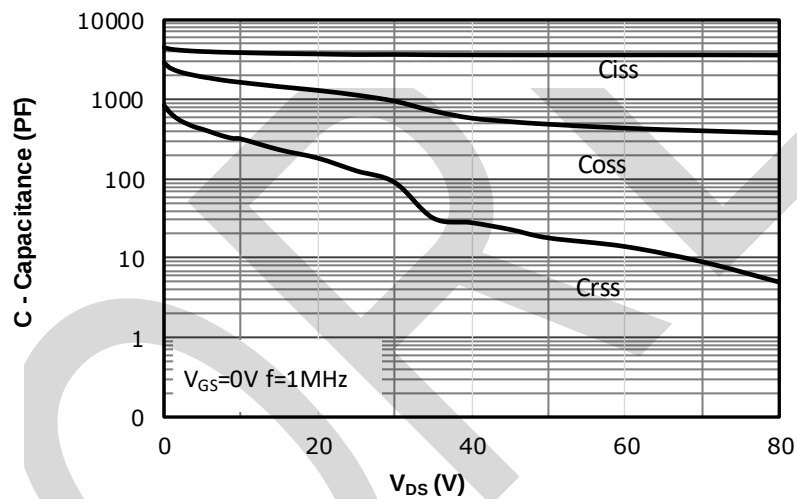
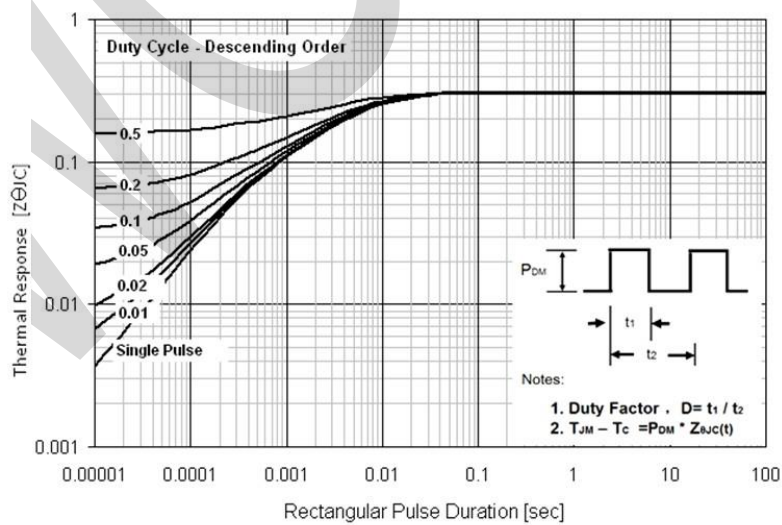
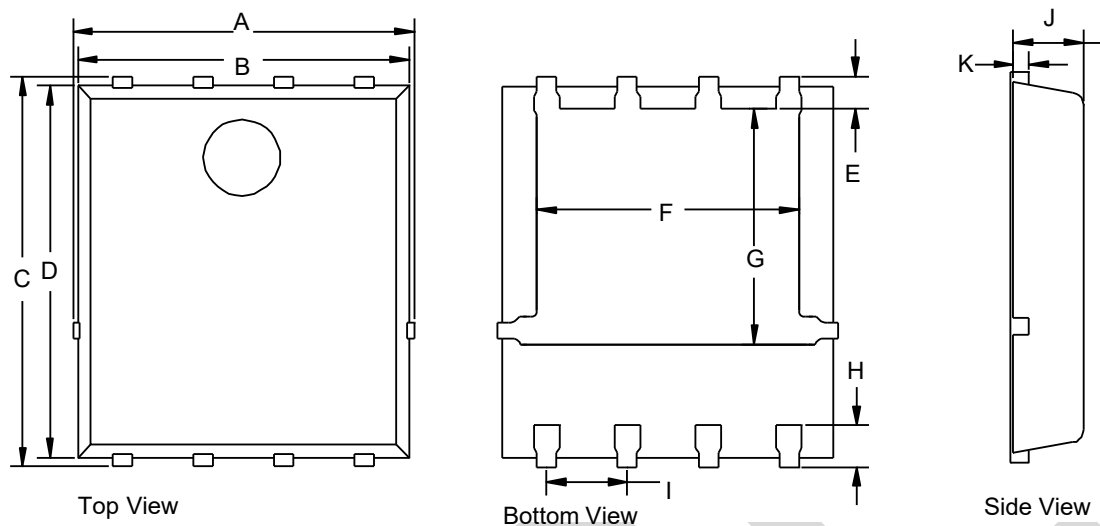


Figure 10: Normalized Maximum Transient Thermal Impedance (R_{thJC})



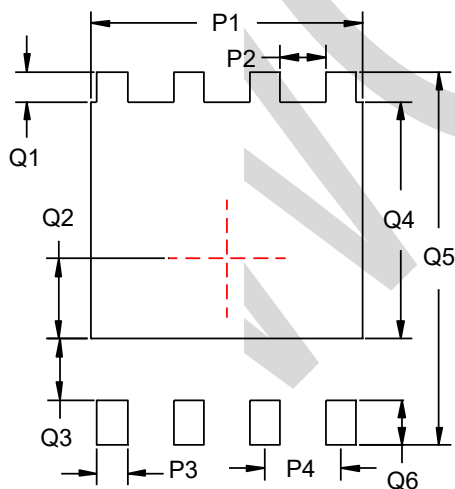
PACKAGE OUTLINE DIMENSIONS



PDFN5x6 mechanical data

UNIT		A	B	C	D	E	F	G	H	I	J	K
mm	min	4.90	4.8	5.90	5.66	0.60	3.90	3.30	0.53	1.27	0.9	0.254
	max	5.55	5.4	6.35	6.06		4.32	3.92	0.76		1.2	
mil	min	192.9	188.9	232.3	222.8	23.6	153.5	129.9	20.8	50.0	35.4	10.0
	max	218.5	212.6	250.0	238.6		170.1	154.3	29.9		47.2	

PDFN5x6 Suggested Pad Layout



UNIT		P1	P2	P3	P4	Q1
mm	min	4.52	0.76	0.51	1.27	0.50
mil	min	177.9	29.9	20.07	50.0	20.0

UNIT		Q2	Q3	Q4	Q5	Q6
mm	min	1.34	1.02	3.97	6.25	0.76
mil	min	52.75	40.15	156.30	246.06	29.92